

EG1AE THRU EG1JE

GLASS PASSIVATED JUNCTION RECTIFIER

VOLTAGE: 50 TO 1000V CURRENT: 0.7A

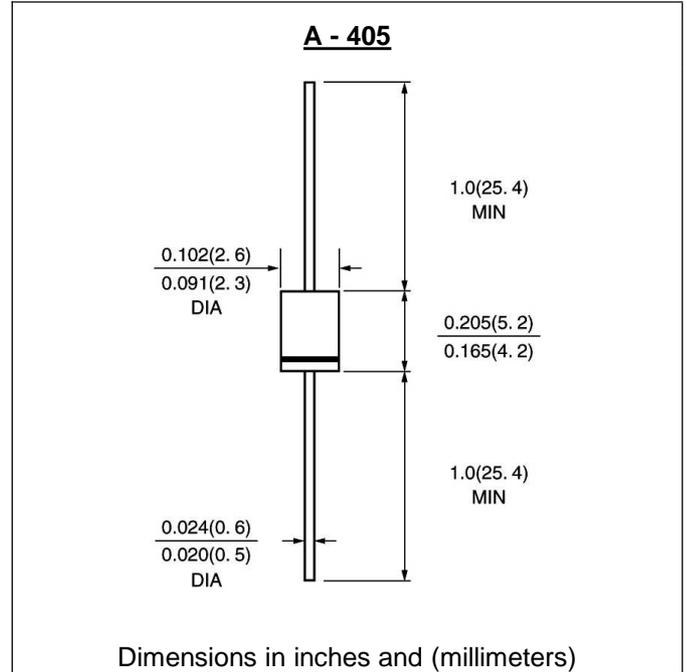


FEATURE

Low power loss
High surge capability
Glass passivated chip junction
Ultra-fast recovery time for high efficiency
High temperature soldering guaranteed
250°C/10sec/0.375" lead length at 5 lbs tension

MECHANICAL DATA

Terminal: Plated axial leads solderable per MIL-STD 202E, method 208C
Case: Molded with UL-94 Class V-0 recognized Flame Retardant Epoxy
Polarity: color band denotes cathode
Mounting position: any



MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

(single-phase, half -wave, 50HZ, resistive or inductive load rating at 25°C, unless otherwise stated)

	SYMBOL	EG1 AE	EG1 BE	EG1 DE	EG1 GE	EG1 JE	units
Maximum Recurrent Peak Reverse Voltage	V _{rrm}	50	100	200	400	600	V
Maximum RMS Voltage	V _{rms}	35	70	140	280	420	V
Maximum DC blocking Voltage	V _{dc}	50	100	200	400	600	V
Maximum Average Forward Rectified Current 3/8" lead length at Ta =55°C	I _{f(av)}	1.0		0.7		0.5	A
Peak Forward Surge Current 10ms single half sine-wave superimposed on rated load	I _{fsm}	30		15		10	A
Maximum Forward Voltage	V _f	1.2 IF=1.0A		2.0 IF=0.7A		2.0 IF=0.5A	V
Maximum DC Reverse Current at rated DC blocking voltage Ta =25°C	I _r	10.0					μ A
Ta =125°C		200.0					μ A
Maximum Reverse Recovery Time (Note 1)	T _{rr}	50					nS
Typical Junction Capacitance (Note 2)	C _j	20			10		pF
Typical Thermal Resistance (Note 3)	R _{th(ja)}	20.0					°C/W
Storage and Operating Junction Temperature	T _{stg,Tj}	-55 to +150					°C

Note:

- Reverse Recovery Condition I_f =0.5A, I_r =1.0A, I_{rr} =0.25A
- Measured at 1.0 MHz and applied reverse voltage of 4.0V_{dc}
- Thermal Resistance from Junction to Ambient at 3/8" lead length, P.C. Board Mounted

